

Docket No.: GR 97 P 1861

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

1c836 U.S. PTO  
09/645807  
08/24/00

Applicant : Volker Weinrich et al.  
Div. of Applic. No. : 09/110,052, filed July 3, 1998  
Div. filed : August 24, 2000  
Title : Method of Producing an Electrode Configuration and Method  
of Electrically Contacting the Electrode Configuration  
Examiner : David B. Hardy Group Art Unit: 2815

INFORMATION DISCLOSURE STATEMENT

Hon. Commissioner of Patents and Trademarks,  
Washington, D.C. 20231

Sir:

In accordance with 37 C.F.R. 1.98 copies of the following patents and/or publications are  
cited herewith:

U.S. Patent No. 4,760,481 (Yuito et al.), dated July 26, 1988;

U.S. Patent No. 5,341,016 (Prall et al.), dated August 23, 1994;

U.S. Patent No. 5,350,705 (Brassington et al.), dated September 27, 1994;

U.S. Patent No. 5,515,984 (Yokoyama et al.), dated May 14, 1996;

U.S. Patent No. 5,562,801 (Nulty), dated October 8, 1996;

U.S. Patent No. 5,585,300 (Summerfelt), dated December 17, 1996;

U.S. Patent No. 5,621,606 (Hwang), dated April 15, 1997;

Patent Abstracts of Japan No. 1-232729 A (Sakota), dated September 18, 1989;

"Etching of TiN local Interconnects Using HBr in a Triode Reactor with Magnetic Confinement" (Zwicker et al.), Proceedings of the International Society for Optical Engineering, Vol. 1803, 1992, pp. 97-106;

"Reactive Ion Etching Mechanism of Plasma Enhanced Chemically Vapor Deposited Aluminum Oxide Film in  $\text{CF}_4/\text{O}_2$  Plasma" (Kim et al.), J. Applied Physics, Vol. 78, No. 3, August 1995, pp. 2045-49;

"Local Plasma Oxidation and Reactive Ion Etching of Metal Films for Ultrafine Line Pattern Inversion and Transfer" (Nulman et al.), J. Vacuum Science Technology, Vol. B1, Oct.-Dec. 1983, pp. 1033-36;

" $\text{WSi}_2$ /Polysilicon Gate Etching Using TiN Hard Mask in Conjunction with Photoresist" (Tabara), J. Applied Physics, Vol. 36, 1997, pp. 2508-13.

Above-mentioned references cited in an Information Disclosure Statement dated July 3, 1998, in parent application No. 09/110,052.

U.S. Patent No. 5,717,236 (Shinkawata), dated February 10, 1998;

U.S. Patent No. 5,883,781 (Yamamichi et al.), dated March 16, 1999;

Above-mentioned references cited in an Office Action dated April 5, 1999, in parent application No. 09/110,052

U.S. Patent No. 5,057,455 (Foo et al.), dated October 15, 1991;

U.S. Patent No. 5,122,225 (Douglas), dated June 16, 1992;

U.S. Patent No. 5,208,170 (Kobeda et al.), dated May 4, 1993.

Above-mentioned references cited in an Information Disclosure Statement dated January 12, 2000, in parent application No. 09/110,052.

If no translation of pertinent portions of any foreign language patents or publications mentioned above is included with the aforementioned copies of those applications, patents and/or publications, it is because no existing translation is readily available to the applicant.

Respectfully submitted,



For Applicants

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Date: August 24, 2000

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